

# MC74VHC138

## 3-to-8 Line Decoder

The MC74VHC138 is an advanced high speed CMOS 3-to-8 decoder fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

When the device is enabled, three Binary Select inputs (A0 – A2) determine which one of the outputs ( $\overline{Y0} - \overline{Y7}$ ) will go Low. When enable input E3 is held Low or either  $\overline{E2}$  or  $\overline{E1}$  is held High, decoding function is inhibited and all outputs go high. E3,  $\overline{E2}$ , and  $\overline{E1}$  inputs are provided to ease cascade connection and for use as an address decoder for memory systems.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

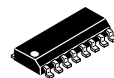
- High Speed:  $t_{PD} = 5.7\text{ns}$  (Typ) at  $V_{CC} = 5\text{V}$
- Low Power Dissipation:  $I_{CC} = 4\ \mu\text{A}$  (Max) at  $T_A = 25^\circ\text{C}$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise:  $V_{OLP} = 0.8\text{V}$  (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 122 FETs or 30.5 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant



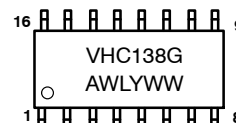
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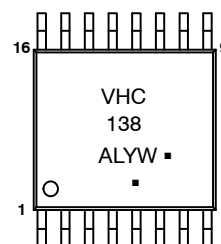
### MARKING DIAGRAMS



**SOIC-16  
D SUFFIX  
CASE 751B**



**TSSOP-16  
DT SUFFIX  
CASE 948F**



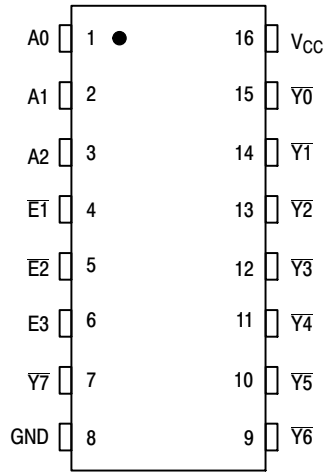
VHC138 = Specific Device Code  
 A = Assembly Location  
 WL, L = Wafer Lot  
 Y = Year  
 WW, W = Work Week  
 G or ■ = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping
MC74VHC138DG	SOIC-16	48 Units/Rail
MC74VHC138DR2G	SOIC-16	2500 Units/Reel
MC74VHC138DTR2G	TSSOP-16	2500 Units/Reel

# MC74VHC138

## PIN ASSIGNMENT

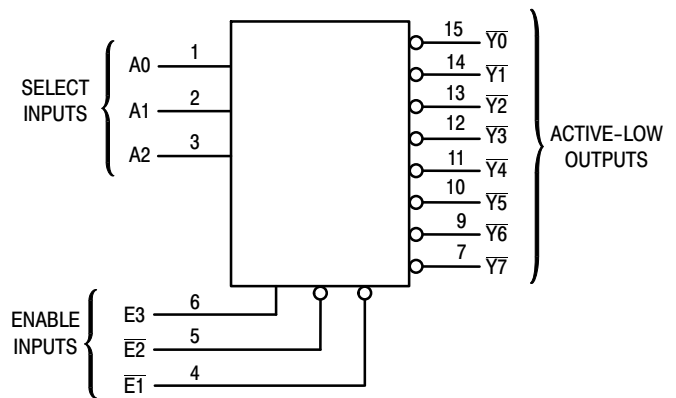


## FUNCTION TABLE

Inputs						Outputs							
E3	E2	E1	A2	A1	A0	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	X	H	X	X	X	H	H	H	H	H	H	H	H
X	H	X	X	X	X	H	H	H	H	H	H	H	H
L	X	X	X	X	X	H	H	H	H	H	H	H	H
H	L	L	L	L	L	L	H	H	H	H	H	H	H
H	L	L	L	L	H	H	L	H	H	H	H	H	H
H	L	L	L	H	L	H	H	L	H	H	H	H	H
H	L	L	L	H	H	H	H	H	H	H	L	H	H
H	L	L	H	H	L	H	H	H	H	H	H	L	H
H	L	L	H	H	H	H	H	H	H	H	H	H	L

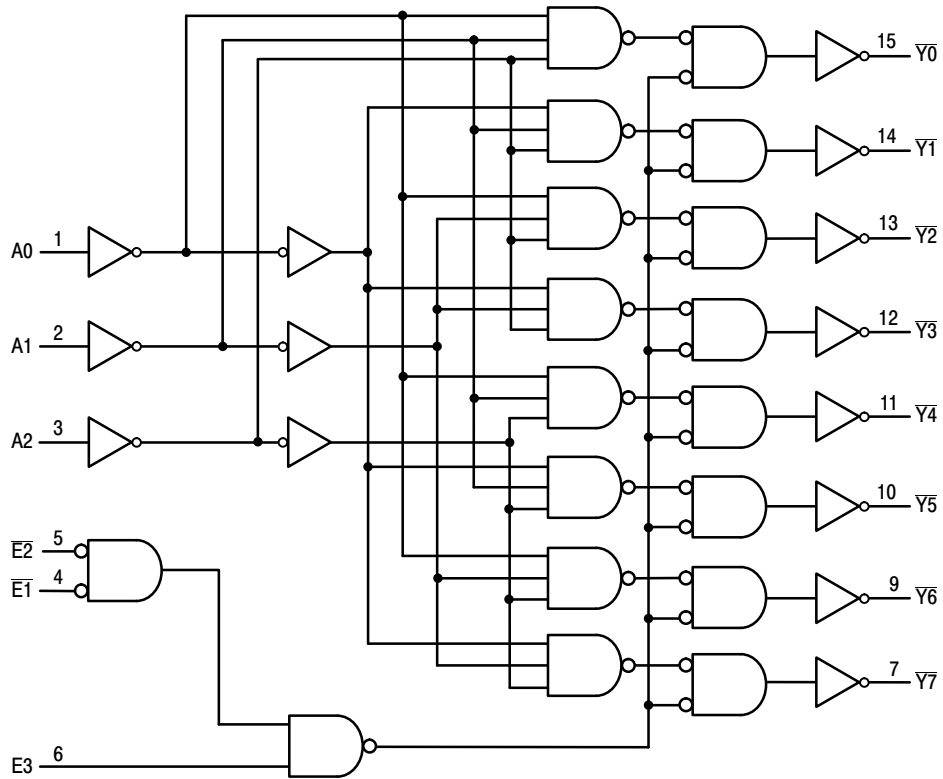
H = high level (steady state); L = low level (steady state);  
X = don't care

## LOGIC DIAGRAM

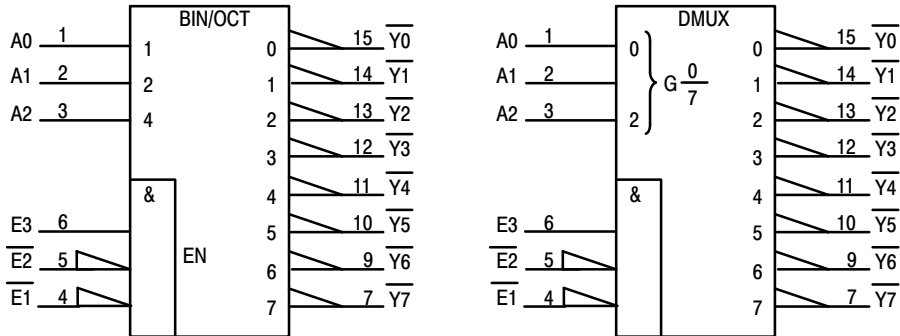


# MC74VHC138

## EXPANDED LOGIC DIAGRAM



## IEC LOGIC DIAGRAM



# MC74VHC138

## MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit
$V_{CC}$	DC Supply Voltage	- 0.5 to + 7.0	V
$V_{in}$	DC Input Voltage	- 0.5 to + 7.0	V
$V_{out}$	DC Output Voltage	- 0.5 to $V_{CC} + 0.5$	V
$I_{IK}$	Input Diode Current	- 20	mA
$I_{OK}$	Output Diode Current	$\pm 20$	mA
$I_{out}$	DC Output Current, per Pin	$\pm 25$	mA
$I_{CC}$	DC Supply Current, $V_{CC}$ and GND Pins	$\pm 75$	mA
$P_D$	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†	500 450	mW
$T_{stg}$	Storage Temperature	- 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

\* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

† Derating — SOIC Packages: - 7 mW/°C from 65° to 125°C  
TSSOP Package: - 6.1 mW/°C from 65° to 125°C

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
$V_{CC}$	DC Supply Voltage	2.0	5.5	V
$V_{in}$	DC Input Voltage	0	5.5	V
$V_{out}$	DC Output Voltage	0	$V_{CC}$	V
$T_A$	Operating Temperature	- 55	+ 125	°C
$t_r, t_f$	Input Rise and Fall Time $V_{CC} = 3.3V \pm 0.3V$ $V_{CC} = 5.0V \pm 0.5V$	0	100 20	ns/V

The  $\theta_{JA}$  of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

## DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

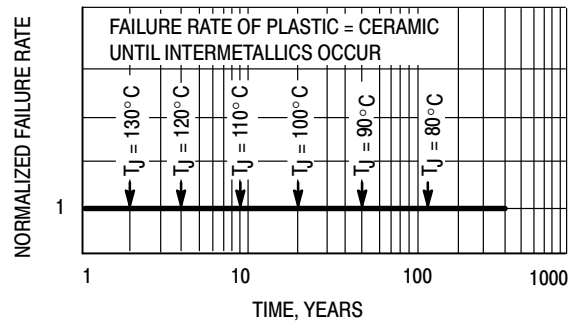


Figure 1. Failure Rate vs. Time Junction Temperature

# MC74VHC138

## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V <sub>CC</sub> (V)	T <sub>A</sub> = 25°C			T <sub>A</sub> = ≤ 85°C		T <sub>A</sub> = ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85	V	
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V <sub>OH</sub>	Minimum High-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = - 50 μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = - 4 mA I <sub>OH</sub> = - 8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V <sub>OL</sub>	Maximum Low-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 50 μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 4 mA I <sub>OL</sub> = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		± 1.0	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			4.0		40.0		40.0	μA

## AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0ns)

Symbol	Parameter	Test Conditions	T <sub>A</sub> = 25°C			T <sub>A</sub> = - 40 to 85°C		T <sub>A</sub> = - 55 to 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A to Y	V <sub>CC</sub> = 3.3 ± 0.3V C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		8.2 10.0	11.4 15.8	1.0 1.0	13.5 18.0	1.0 1.0	13.5 18.0	ns
		V <sub>CC</sub> = 5.0 ± 0.5V C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		5.7 7.2	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, E3 to Y	V <sub>CC</sub> = 3.3 ± 0.3V C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		8.1 10.6	12.8 16.3	1.0 1.0	15.0 18.5	1.0 1.0	15.0 18.5	ns
		V <sub>CC</sub> = 5.0 ± 0.5V C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		5.6 7.1	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, E2 or E1 to Y	V <sub>CC</sub> = 3.3 ± 0.3V C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		8.2 10.7	11.4 14.9	1.0 1.0	13.5 17.0	1.0 1.0	13.5 17.0	ns
		V <sub>CC</sub> = 5.0 ± 0.5V C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		5.8 7.3	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
C <sub>IN</sub>	Maximum Input Capacitance			4	10		10		10	pF

C <sub>PD</sub>	Power Dissipation Capacitance (Note 1)	Typical @ 25°C, V <sub>CC</sub> = 5.0V		pF
		34		

1. C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

# MC74VHC138

## SWITCHING WAVEFORMS

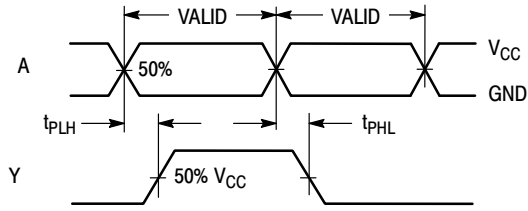


Figure 2.

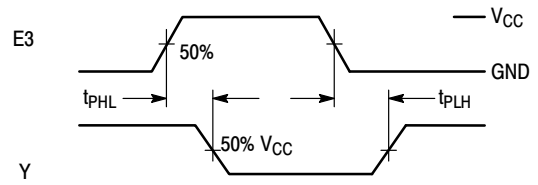


Figure 3.

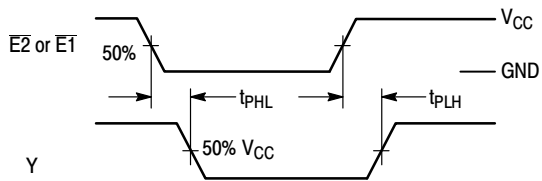
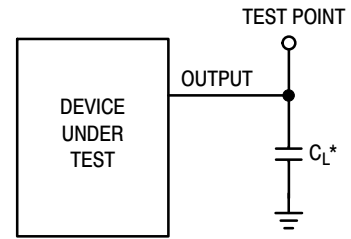


Figure 4.



\*Includes all probe and jig capacitance

Figure 5. Test Circuit

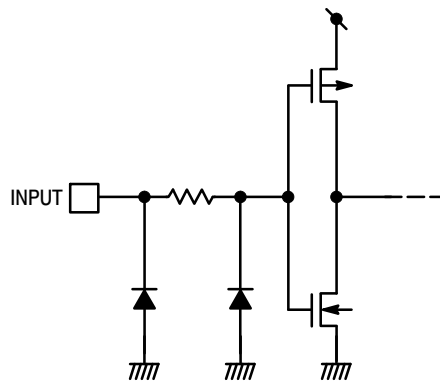


Figure 6. Input Equivalent Circuit

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1

## SOIC-16 CASE 751B-05 ISSUE K

DATE 29 DEC 2006



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

- |  |  |  |  |
|--|--|--|--|
| <p><b>STYLE 1:</b></p> <p>PIN 1. COLLECTOR<br/>2. BASE<br/>3. EMITTER<br/>4. NO CONNECTION<br/>5. EMITTER<br/>6. BASE<br/>7. COLLECTOR<br/>8. COLLECTOR<br/>9. BASE<br/>10. EMITTER<br/>11. NO CONNECTION<br/>12. EMITTER<br/>13. BASE<br/>14. COLLECTOR<br/>15. EMITTER<br/>16. COLLECTOR</p>                           | <p><b>STYLE 2:</b></p> <p>PIN 1. CATHODE<br/>2. ANODE<br/>3. NO CONNECTION<br/>4. CATHODE<br/>5. CATHODE<br/>6. NO CONNECTION<br/>7. ANODE<br/>8. CATHODE<br/>9. CATHODE<br/>10. ANODE<br/>11. NO CONNECTION<br/>12. CATHODE<br/>13. CATHODE<br/>14. NO CONNECTION<br/>15. ANODE<br/>16. CATHODE</p> | <p><b>STYLE 3:</b></p> <p>PIN 1. COLLECTOR, DYE #1<br/>2. BASE, #1<br/>3. EMITTER, #1<br/>4. COLLECTOR, #1<br/>5. COLLECTOR, #2<br/>6. BASE, #2<br/>7. EMITTER, #2<br/>8. COLLECTOR, #2<br/>9. COLLECTOR, #3<br/>10. BASE, #3<br/>11. EMITTER, #3<br/>12. COLLECTOR, #3<br/>13. COLLECTOR, #4<br/>14. BASE, #4<br/>15. EMITTER, #4<br/>16. COLLECTOR, #4</p>   | <p><b>STYLE 4:</b></p> <p>PIN 1. COLLECTOR, DYE #1<br/>2. COLLECTOR, #1<br/>3. COLLECTOR, #2<br/>4. COLLECTOR, #2<br/>5. COLLECTOR, #3<br/>6. COLLECTOR, #3<br/>7. COLLECTOR, #4<br/>8. COLLECTOR, #4<br/>9. BASE, #4<br/>10. EMITTER, #4<br/>11. BASE, #3<br/>12. EMITTER, #3<br/>13. BASE, #2<br/>14. EMITTER, #2<br/>15. BASE, #1<br/>16. EMITTER, #1</p> |
| <p><b>STYLE 5:</b></p> <p>PIN 1. DRAIN, DYE #1<br/>2. DRAIN, #1<br/>3. DRAIN, #2<br/>4. DRAIN, #2<br/>5. DRAIN, #3<br/>6. DRAIN, #3<br/>7. DRAIN, #4<br/>8. DRAIN, #4<br/>9. GATE, #4<br/>10. SOURCE, #4<br/>11. GATE, #3<br/>12. SOURCE, #3<br/>13. GATE, #2<br/>14. SOURCE, #2<br/>15. GATE, #1<br/>16. SOURCE, #1</p> | <p><b>STYLE 6:</b></p> <p>PIN 1. CATHODE<br/>2. CATHODE<br/>3. CATHODE<br/>4. CATHODE<br/>5. CATHODE<br/>6. CATHODE<br/>7. CATHODE<br/>8. CATHODE<br/>9. ANODE<br/>10. ANODE<br/>11. ANODE<br/>12. ANODE<br/>13. ANODE<br/>14. ANODE<br/>15. ANODE<br/>16. ANODE</p>                                 | <p><b>STYLE 7:</b></p> <p>PIN 1. SOURCE N-CH<br/>2. COMMON DRAIN (OUTPUT)<br/>3. COMMON DRAIN (OUTPUT)<br/>4. GATE P-CH<br/>5. COMMON DRAIN (OUTPUT)<br/>6. COMMON DRAIN (OUTPUT)<br/>7. COMMON DRAIN (OUTPUT)<br/>8. SOURCE P-CH<br/>9. SOURCE P-CH<br/>10. COMMON DRAIN (OUTPUT)<br/>11. COMMON DRAIN (OUTPUT)<br/>12. COMMON DRAIN (OUTPUT)<br/>13. GATE N-CH<br/>14. COMMON DRAIN (OUTPUT)<br/>15. COMMON DRAIN (OUTPUT)<br/>16. SOURCE N-CH</p> |  |

### SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



TSSOP-16  
CASE 948F-01  
ISSUE B

DATE 19 OCT 2006



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM\*



- XXXX = Specific Device Code
- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- G or ■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

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